

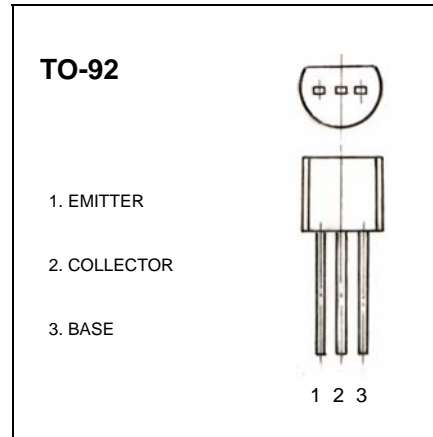
# 深圳市晶泰源电子有限公司

**A562**

TRANSISTOR (PNP)

**FEATURES**

- Excellent  $h_{FE}$  linearity



**MAXIMUM RATINGS ( $T_A=25^{\circ}C$  unless otherwise noted)**

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	-35	V
$V_{CEO}$	Collector-Emitter Voltage	-30	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current -Continuous	-500	mA
$P_C$	Collector Power Dissipation	500	mW
$T_j$	Junction Temperature	150	$^{\circ}C$
$T_{stg}$	Storage Temperature	-55-150	$^{\circ}C$

**ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^{\circ}C$  unless otherwise specified)**

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	$I_C = -100\mu A, I_E = 0$	-35			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	$I_C = -1mA, I_B = 0$	-30			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	$I_E = -100\mu A, I_C = 0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -35V, I_E = 0$			-0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -5V, I_C = 0$			-0.1	$\mu A$
DC current gain	$h_{FE}$	$V_{CE} = -1V, I_C = -100mA$	70		240	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100mA, I_B = -10mA$			-0.25	V
Base-emitter voltage	$V_{BE}$	$V_{CE} = -1V, I_C = -100mA$			-1	V
Transition frequency	$f_T$	$V_{CE} = -6V, I_C = -20mA$		200		MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = -6V, I_E = 0, f = 1MHz$		13		pF

**CLASSIFICATION OF  $h_{FE}$**

Rank		Y
Range		120-240